

# Microwave sintering of $\text{Ba}_{0,6}\text{Sr}_{0,4}\text{TiO}_3$ Thick-Films

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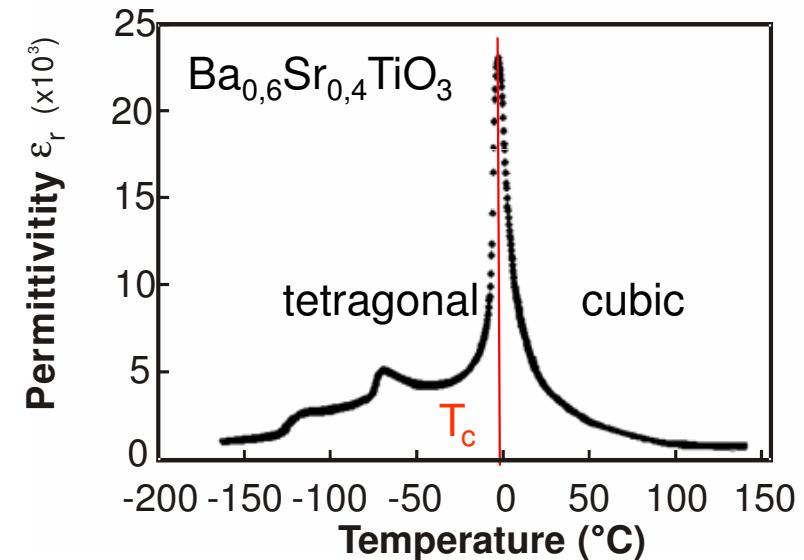
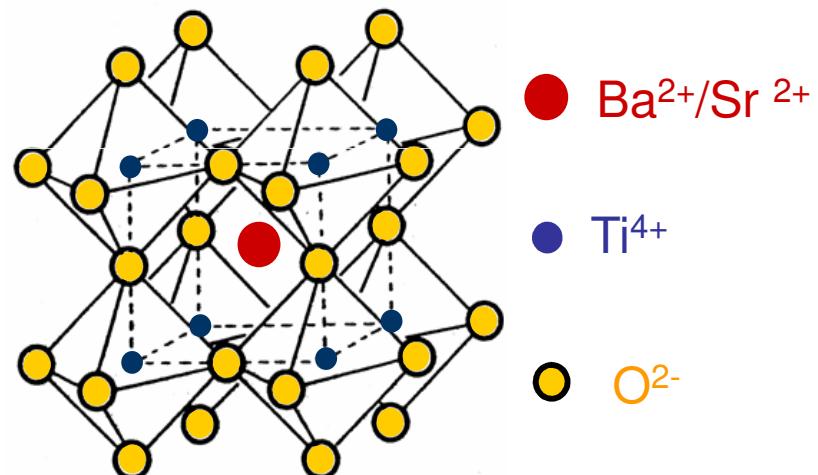
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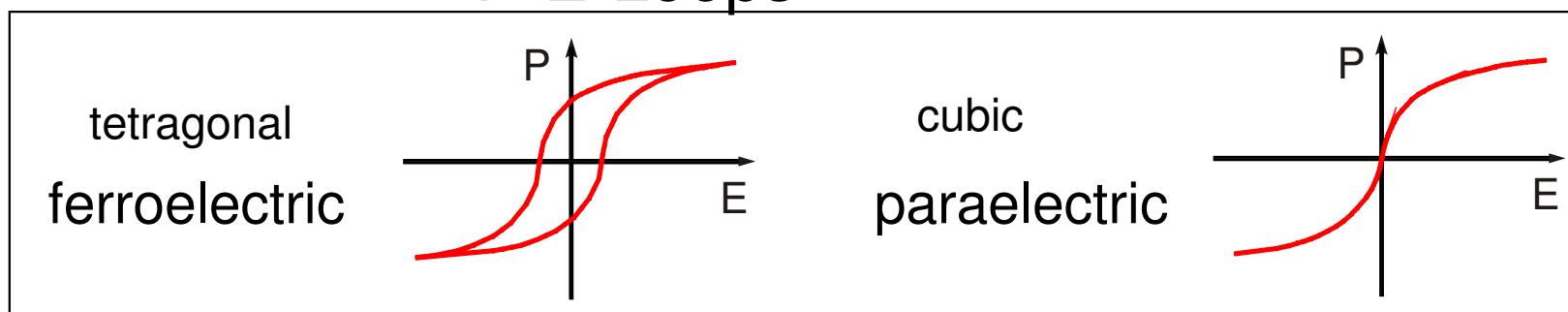


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# Introduction



## P-E-Loops

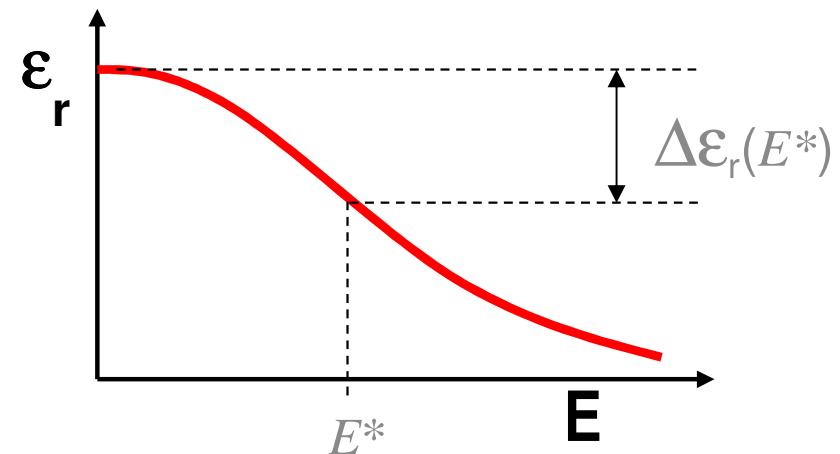
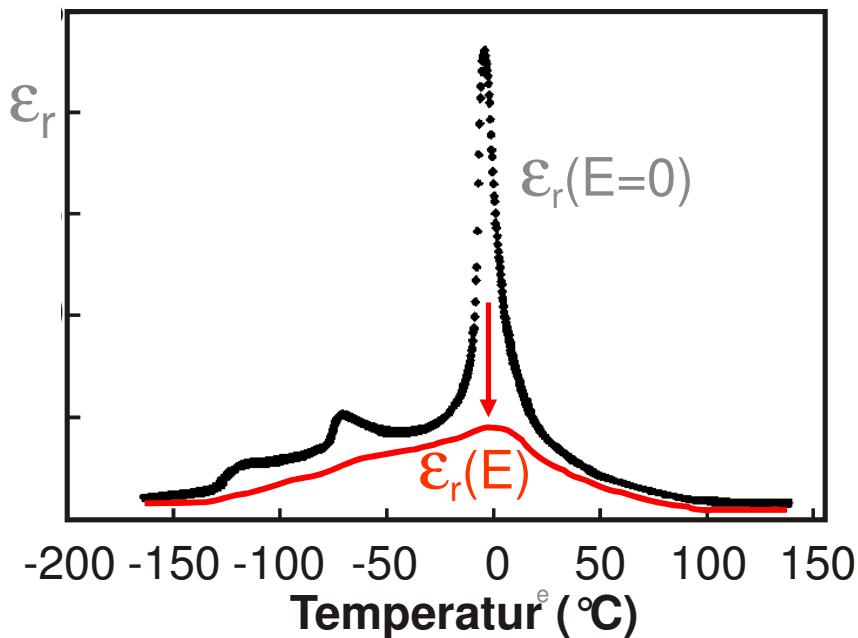


# Introduction

## Decrease of permittivity

tunability : decrease of permittivity through external el. field

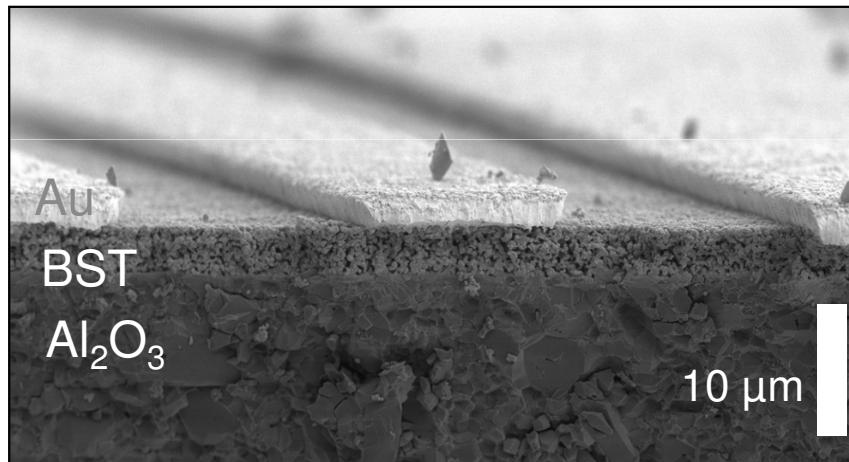
$$\text{tunability } \tau(E^*) = \frac{\Delta\epsilon_r(E^*)}{\epsilon_r(E=0)}$$



# Motivation

## functionality

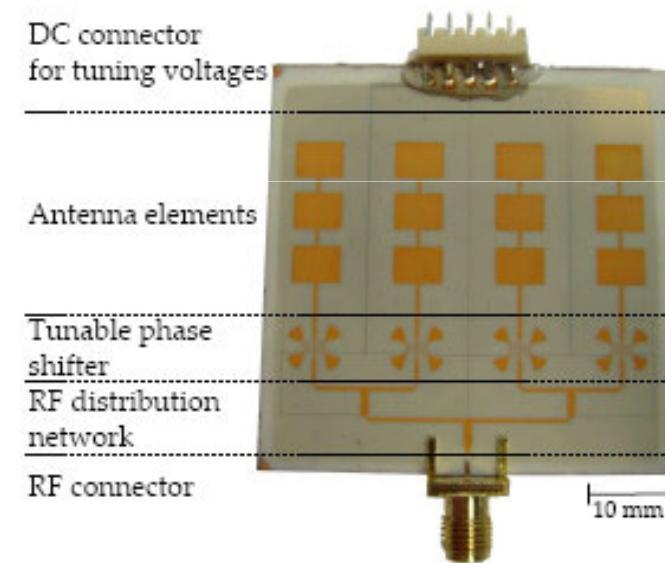
- permittivity of  $\text{Ba}_{0.6}\text{Sr}_{0.4}\text{TiO}_3$  shows nonlinear tunability under static E-field



cross-section of coplanar  
waveguide

## application

- tunable RF-components
- reconfigurable circuits
- phaseshifters (delay lines)
- electronically steerable oscillators & filters



passive phase array antenna

# Microwave sintering (MWS)

conventional



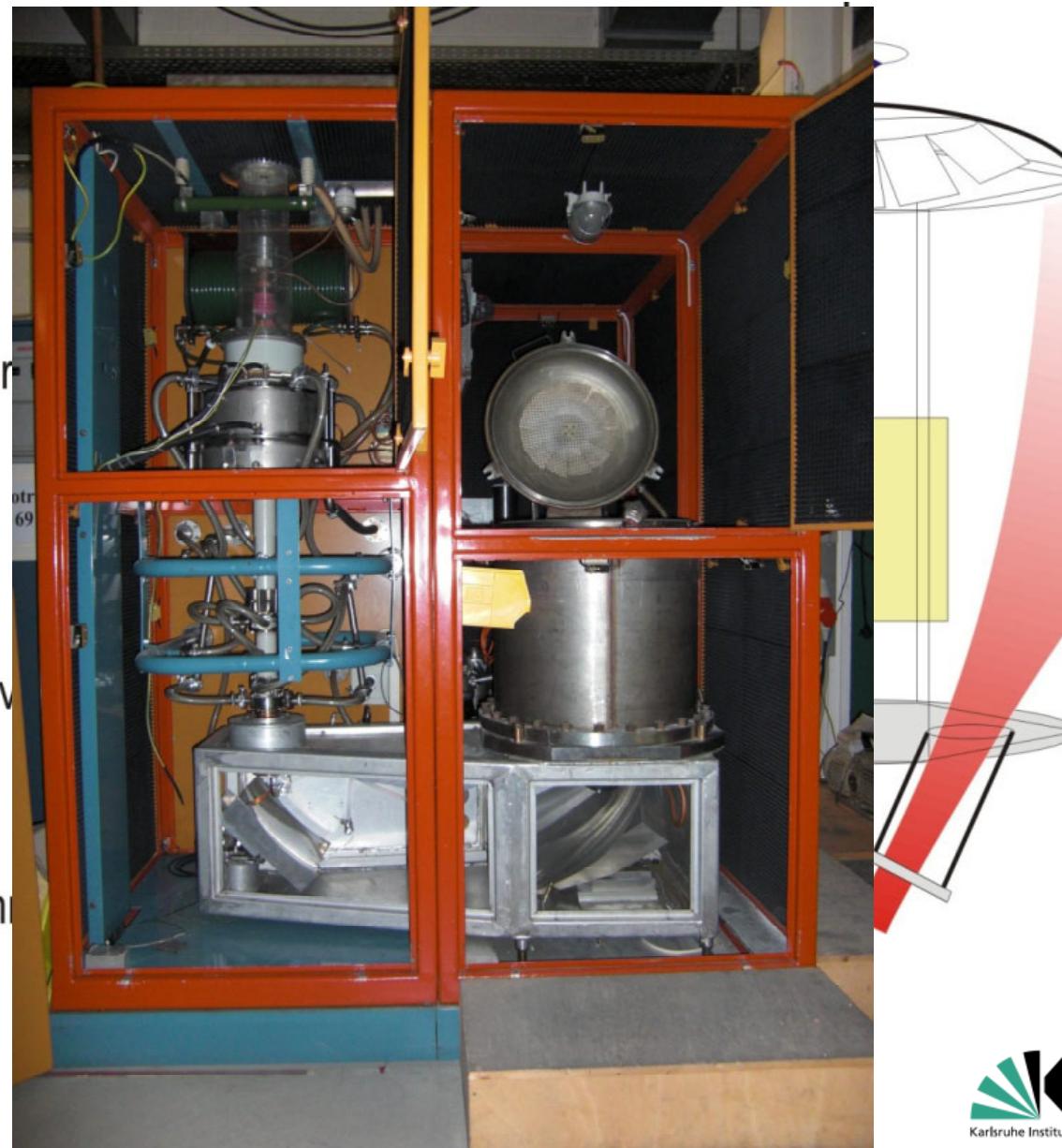
- heating from „outside“ in conventional sintering

microwave

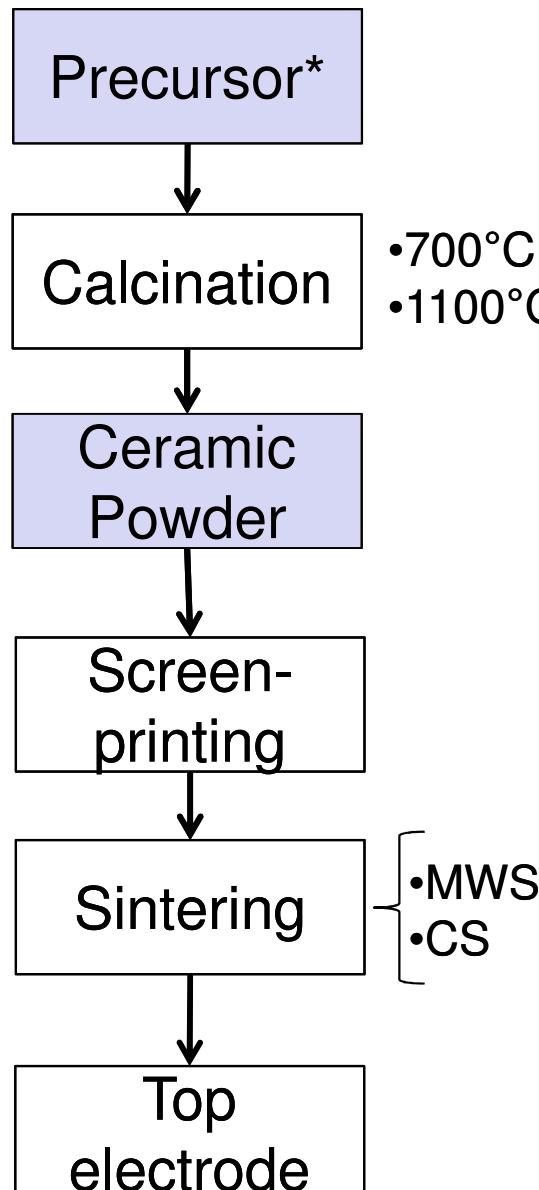


- inverse heating profile in MWS
- regions with high dielectric loss heat up stronger
- short processing time and high heating rates

# Microwave sintering (MWS)

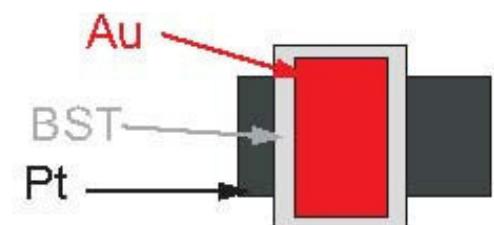
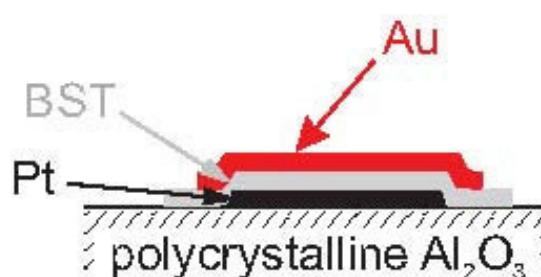


# Specimen fabrication



## thermal treatments in air

Name of specimen	Calcination temperature (CT)	conventional sintering (CS)	microwave sintering (MWS)
heating	5 K/min	5 K/min	20 K/min
cooling	max. 10 K/min	5 K/min	5 K/min
BST-CT700-CS	700°C, 1h	1200°C, 1h	-
BST-CT1100-CS	1100°C, 1h	1200°C, 1h	-
BST-CT700-MWS	700°C, 1h	-	1200°C, 20 min

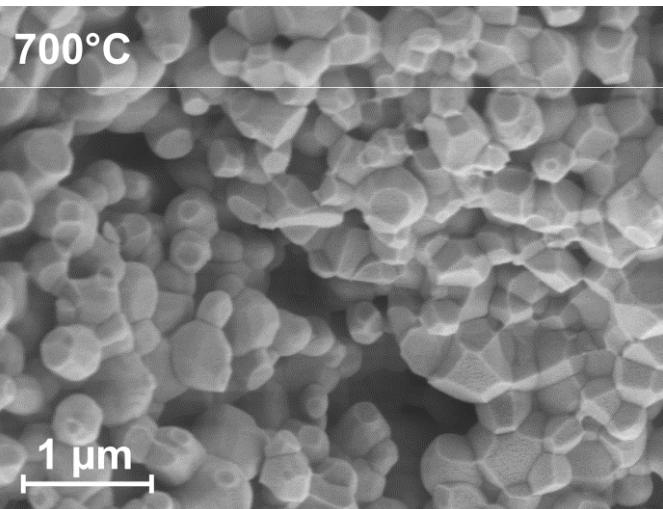


MWS: Microwave sintering  
CS: conventional sintering

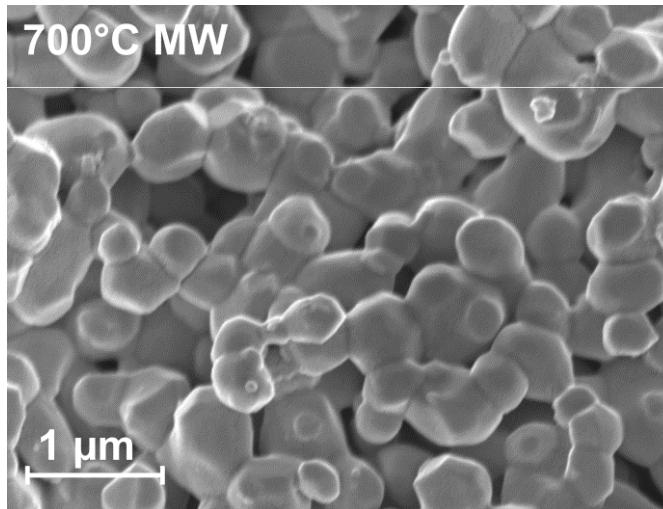
# Microstructure

## SEM cross-sections

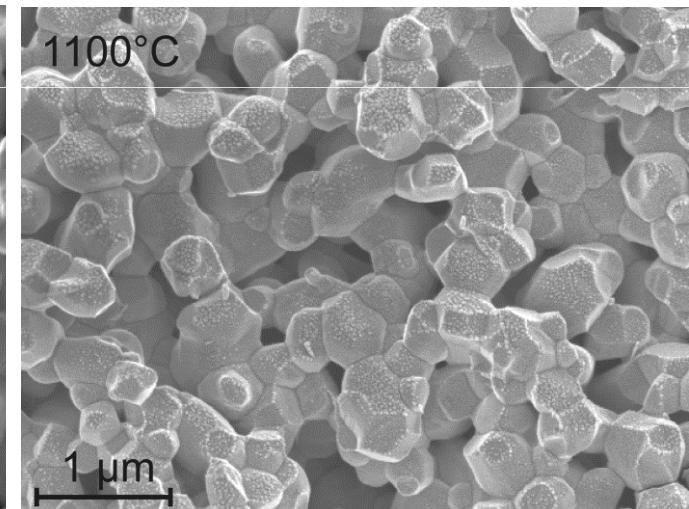
BST-CT700-CS



BST-CT700-MWS



BST-CT1100-CS



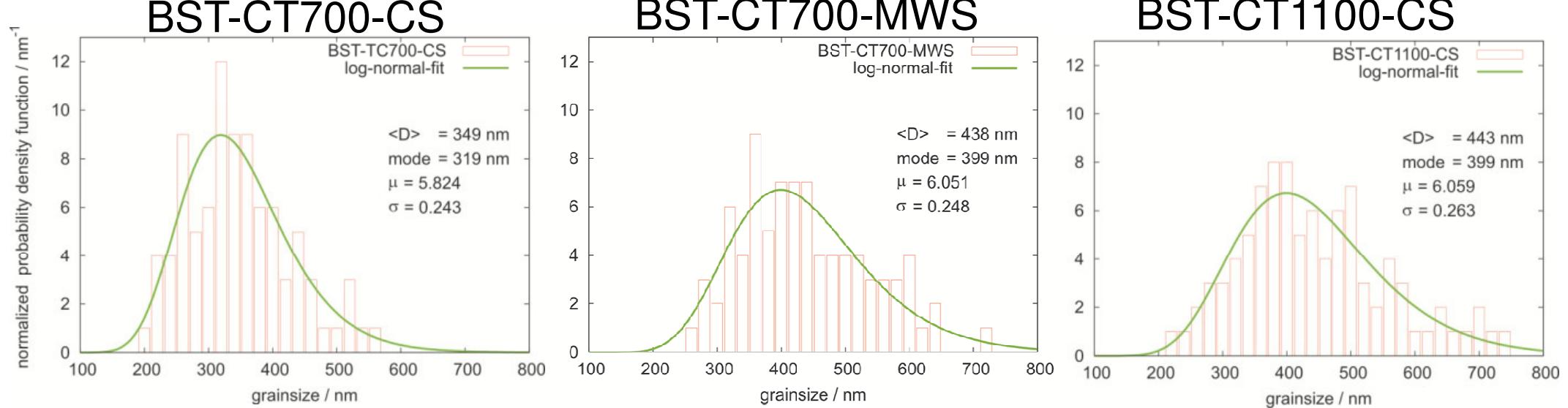
- calcined 700°C, 1h
- sintered conventionally 1200°C, 1h

- Calcined 700°C
- sintered by microwave (30 GHz) 1200°C, 20Min.

- calcined 1100°C, 1h
- sintered conventionally 1200°C, 1h

# Microstructure

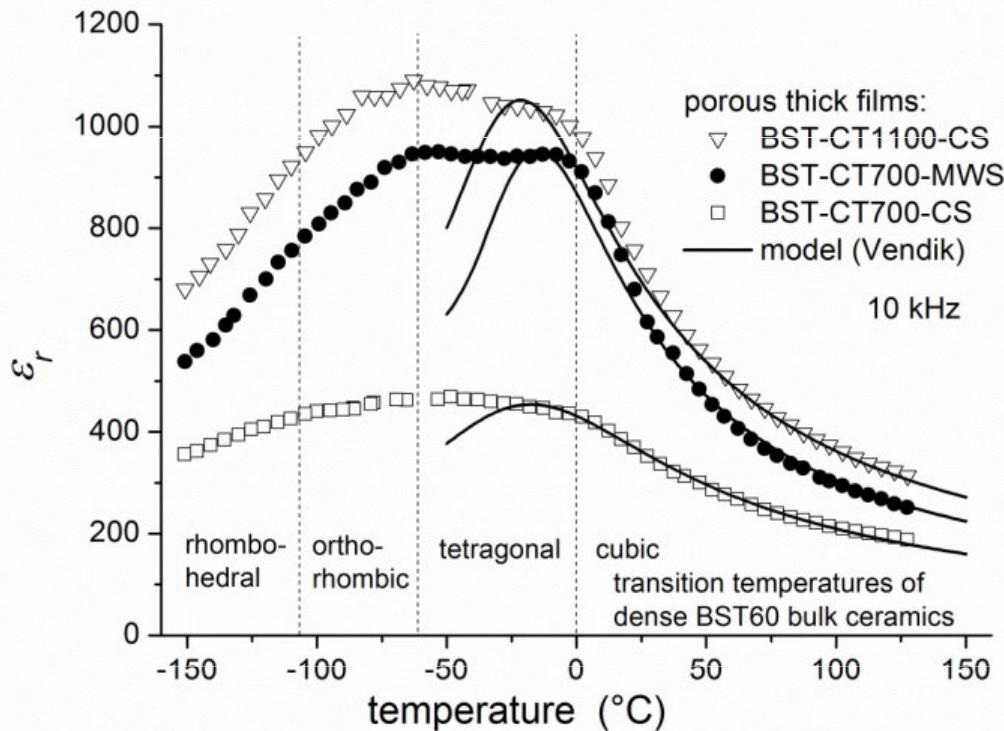
## grain sizes and porosities



name of film / sample	mean grain size $\langle D \rangle$ (nm)	$\sigma_D$ (nm)	mode (nm)	porosity (%)	thickness (μm)
BST-CT700-CS	349	85	319	41	10,5
BST-CT700-MWS	438	109	399	34	15,5
BST-CT1100-CS	443	116	399	33	19

# Dielectric properties

## Permittivity



- Low  $\epsilon_r$  compared to bulk ceramics
- Decreased temperature dependence
- Broad phase transition peaks
- High calcination Temp.: increases  $\epsilon_r$
- MWS.: increases  $\epsilon_r$
- $T_c$  is shifted to lower temperatures

modelling of the dielectric data after O. G. Vendik, S. P. Zubko, Journal of Applied Physics, 88(2000) 5343-5350

# Dielectric properties

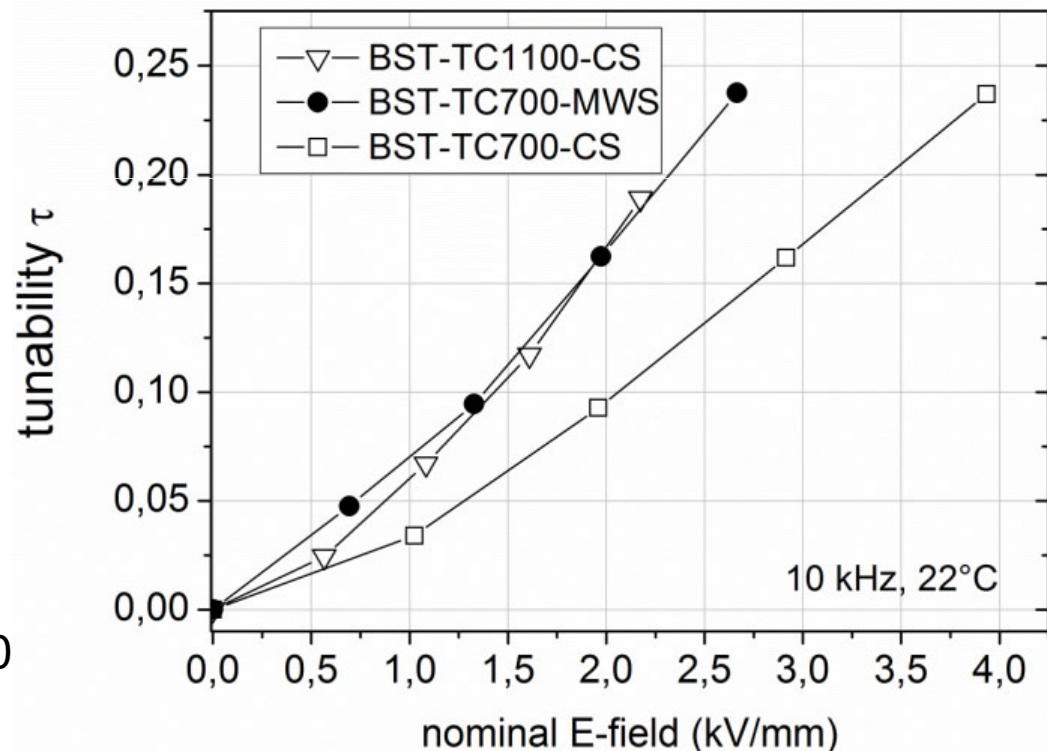
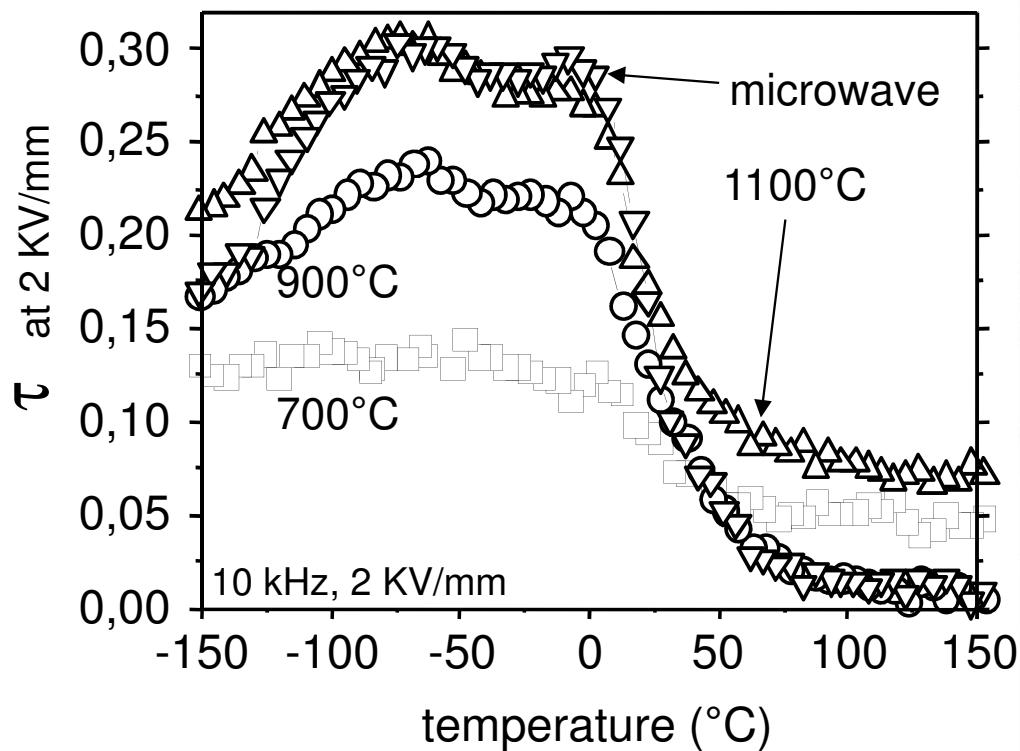
## fitted parameters (Vendik model)

	$T_c$ / K ( $\pm 3$ )	$\xi_s$ ( $\pm 0.005$ )	mean grain size / nm	porosity / %
BST-CT700-CS	223	0.13	349	41
BST-CT700-MWS	240	0.055	438	34
BST-CT110-CS	230	0.073	443	33
BST60 ceramic	270	0.01*	-	-

- higher crystal quality after CT= 1100°C and MWS
- more bulky behavior after CT= 1100°C and MWS ( $T_c$ ,  $\xi_s$ )
- \*BST60 bulk-ceramics exhibit much lower values of  $\xi_s$  as suggested by Vendik ( $\xi_s > 0.1$ )

# Dielectric properties

## tunability



- high tunability due to high calcination temperature and microwave sintering
- increased tunability, compared to bulk ceramics with similar grain size

# Conclusion

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- thermal treatment plays a crucial role in processing of BST ceramics and thick films
- Dielectric properties are heavily dependent on microstructure and crystal quality
- porous BST thick films show decreased
  - permittivity
  - $T_c$
  - temperature dependence
  - cristal quality as bulk ceramics
- MWS is a high impact sintering method, comparable to long lasting conventional heating and sintering

# Thank you for your attention

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Thank you for collaboration and help:

- Dr. Meneskou, Dr. Binder, Dr. Link, Dr. Zhou, Karlsruhe Institute of Technology The KIT logo features the letters "KIT" in a bold, black, sans-serif font. To the left of "KIT" are three stylized green and blue fan-like shapes. Below the letters is the text "Karlsruhe Institute of Technology".
- Prof. R. Jakoby, Dr. H. Maune, Dr. Giere, Microwave Engineering, University of Darmstadt The University of Darmstadt logo is a circular emblem featuring a profile of a head, possibly a Greek or Roman figure, with intricate patterns in the background. To the right of the emblem, the text "TECHNISCHE UNIVERSITÄT DARMSTADT" is written in a serif font.

These results will be published in the Proceedings of ISIF 2012